

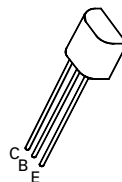
NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

ZTX449

ISSUE 2 – MARCH 1994

FEATURES

- * 30 Volt V_{CEO}
- * 1 Amp continuous current
- * P_{tot} = 1 Watt



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^\circ\text{C}$

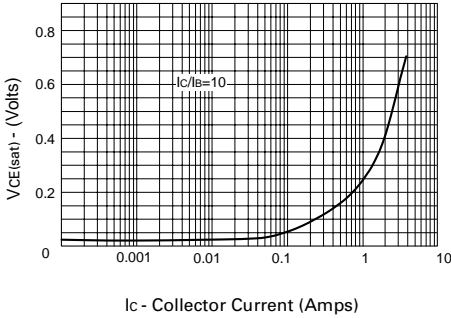
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50			V	$I_C = 100\mu\text{A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_C = 10\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E = 100\mu\text{A}$, $I_C = 0$
Collector Cut-Off Current	I_{CBO}			0.1 10	μA	$V_{CB} = 40\text{V}$ $V_{CB} = 40\text{V}$, $T_{amb} = 100^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB} = 4\text{V}$, $I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5 1	V	$I_C = 1\text{A}$, $I_B = 100\text{mA}^*$ $I_C = 2\text{A}$, $I_B = 200\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.25	V	$I_C = 1\text{A}$, $I_B = 100\text{mA}^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$			1	V	$I_C = 1\text{A}$, $V_{CE} = 2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	70 100 80 40		300		$I_C = 50\text{mA}$, $V_{CE} = 2\text{V}^*$ $I_C = 500\text{mA}$, $V_{CE} = 2\text{V}^*$ $I_C = 1\text{A}$, $V_{CE} = 2\text{V}^*$ $I_C = 2\text{A}$, $V_{CE} = 2\text{V}^*$
Transition Frequency	f_T	150			MHz	$I_C = 50\text{mA}$, $V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}			15	pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$

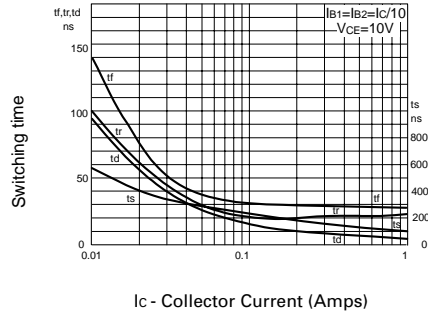
*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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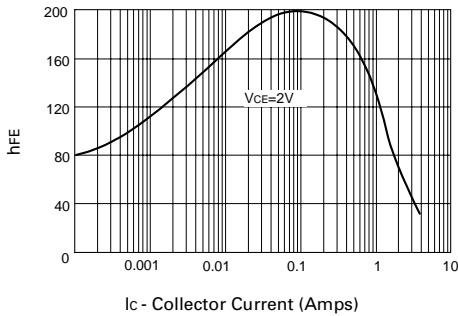
TYPICAL CHARACTERISTICS



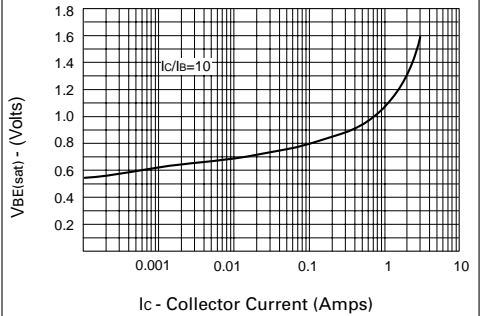
$V_{CE(sat)}$ v I_C



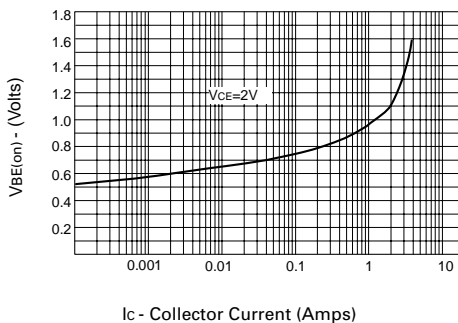
Switching Speeds



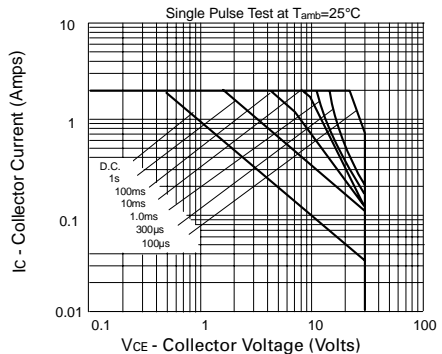
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area